



### 100V PNP LOW SATURATION TRANSISTOR IN U-DFN2020-3

### **Features**

- BVcEo > -100V
- hFE Specified up to -3A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

## **Mechanical Data**

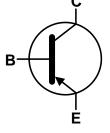
- Case: U-DFN2020-3 (Type B)
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.01 grams (Approximate)

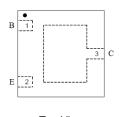
### **Applications**

- DC-DC Converters
- Charging Circuits
- Motor Control
- **Power Switches**









Device Symbol

Top View Pin-Out

### **Ordering Information** (Note 4)

Top View

	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
DXTP58100CFDB-7		2E6	7	8	3,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

**Bottom View** 

# **Marking Information**



2E6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019)M = Month (ex: 9 = September)

Date Code Kev

Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н			J	K		L	M		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	Vcво	-100	
Collector-Emitter Voltage	Vceo	-100	V
Emitter-Base Voltage	VEBO	-7	
Peak Pulse Current	Ісм	-4	^
Continuous Collector Current	Ic	-2	A

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	D-	0.69	W	
Power Dissipation	(Note 6)	P <sub>D</sub>	1.25		
Thermal Decistores, Junction to Ambient	(Note 5)	-	180	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	100		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

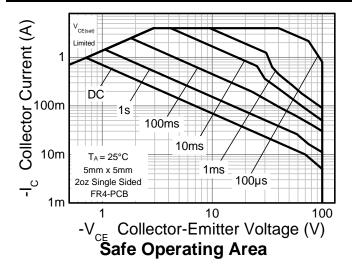
Notes:

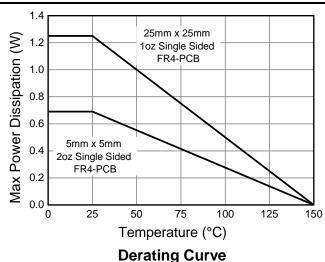
<sup>5.</sup> For a device mounted with the exposed collector on 5mm x 5mm 2oz copper on single sided FR4 PCB; device is measured under still air conditions whilst operating in the steady state.

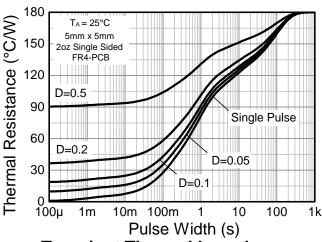
<sup>6.</sup> Same as Note (5) except the exposed collector pad is mounted on 25mm x 25mm 1oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

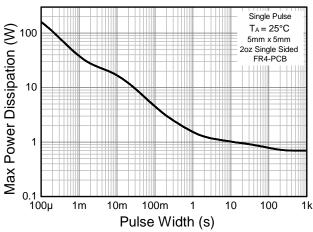


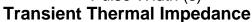
## Thermal Characteristics and Derating Information



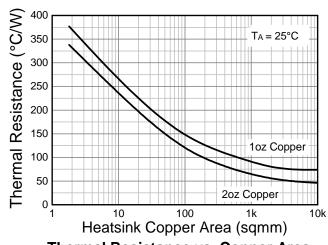


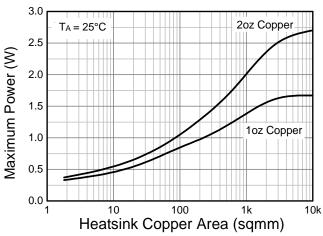






**Pulse Power Dissipation** 





Thermal Resistance vs. Copper Area

Max Power Dissipation vs. Copper Area



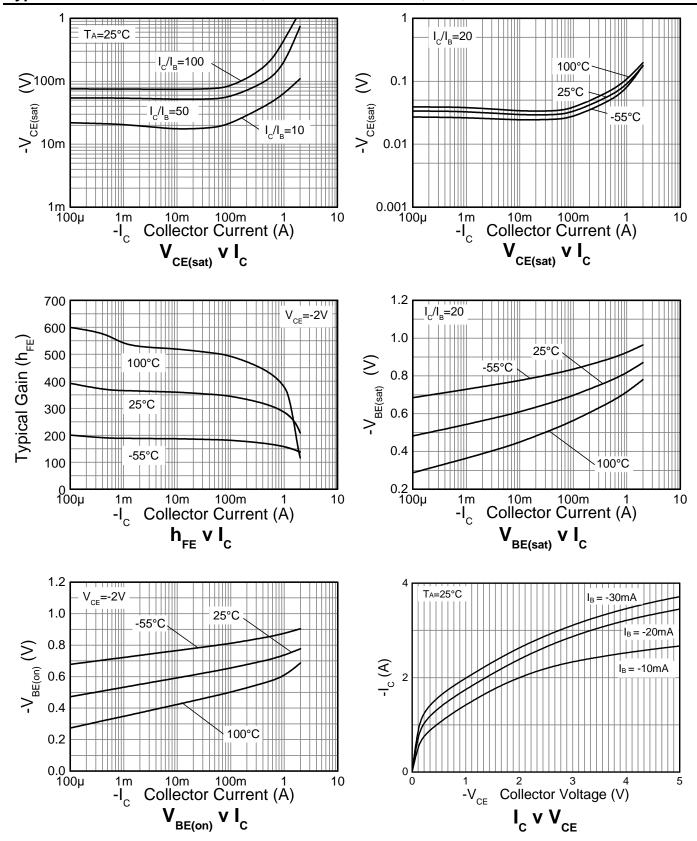
# Electrical Characteristics (@TA = +25°C, unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	-100	_	_	V	Ic = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	-100	_	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	Ісво	_	_	-100	nA	V <sub>CB</sub> = -80V
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	V <sub>EB</sub> = -6V
Collector Emitter Cutoff Current	I <sub>CES</sub>	_	_	-100	nA	V <sub>CES</sub> = -80V
		160	260	_		Ic = -500mA, VcE = -2V
Static Forward Current Transfer Ratio (Note 8)	hfe	150	240	_		Ic = -1A, VcE = -2V
Static Forward Current Transfer Ratio (Note 6)	IIFE	90	180	_	_	Ic = -2A, VcE = -2V
		15	60	_		Ic = -3A, VcE = -2V
		_	-45	-70	mV	I <sub>C</sub> = -0.5A, I <sub>B</sub> = -50mA
Collector-Emitter Saturation Voltage (Note 8)	VCE(sat)	_	-95	-150		I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA
		_	-125	-185		I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(on)}$	_	-0.75	-0.9	V	I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE</sub> (sat)	_	-0.75	-0.9	V	$I_C = -1A$ , $I_B = -10mA$
Output Capacitance	Cobo	_	30	_	pF	$V_{CB} = -10V$ , $f = 1MHz$
Transition Frequency	fτ	_	135	_	MHz	VcE = -10V, Ic = -100mA, f = 100MHz
Delay Time	td	_	15	_		
Rise Time	t <sub>r</sub>	_	60	_		
Turn-On Time	ton	_	75	_		Vcc = -9V, Ic = -2A
Storage Time	ts	_	485	_	ns	$I_{B1} = -I_{B2} = -0.1A$
Fall Time	t <sub>f</sub>	_	155	_		
Turn-Off Time	toff	_	640			

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

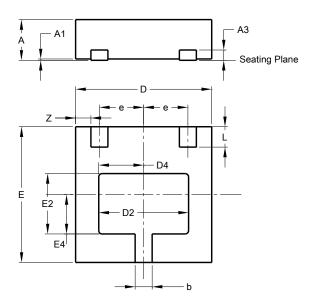




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-3 (Type B)

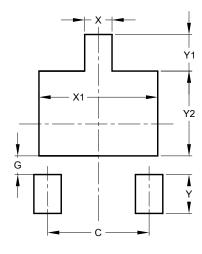


U-DFN2020-3 (Type B)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.02				
А3			0.152				
b	0.20	0.30	0.25				
D	1.950	2.075	2.00				
D2	1.22	1.42	1.32				
D4	0.56	0.76	0.66				
Е	1.950	2.075	2.00				
E2	0.79	0.99	0.89				
E4	0.48	0.68	0.58				
е	_		0.65				
L	0.25	0.35	0.30				
<b>Z</b> — — 0.225							
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-3 (Type B)



Dimensions	Value		
Dilliciisiolis	(in mm)		
С	1.300		
G	0.240		
Х	0.350		
X1	1.520		
Υ	0.500		
Y1	0.470		
Y2	1.090		



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